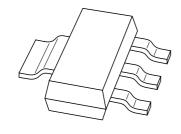
## **DISCRETE SEMICONDUCTORS**

# DATA SHEET



## BSP50; BSP51; BSP52 NPN Darlington transistors

Product data sheet Supersedes data of 1997 Apr 22 1999 Apr 23



## **NPN Darlington transistors**

BSP50; BSP51; BSP52

#### **FEATURES**

- High current (max. 1 A)
- Low voltage (max. 80 V)
- Integrated diode and resistor.

#### **APPLICATIONS**

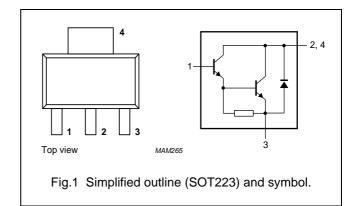
• Industrial high gain amplification.

#### **DESCRIPTION**

NPN Darlington transistor in a SOT223 plastic package. PNP complements: BSP60, BSP61 and BSP62.

#### **PINNING**

PIN	DESCRIPTION
1	base
2,4	collector
3	emitter



#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS		MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BSP50		_	60	V
	BSP51		_	80	V
	BSP52		_	90	V
V <sub>CES</sub>	collector-emitter voltage	V <sub>BE</sub> = 0			
	BSP50		_	45	V
	BSP51		_	60	V
	BSP52		_	80	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	5	V
I <sub>C</sub>	collector current (DC)		_	1	Α
I <sub>CM</sub>	peak collector current		_	2	Α
I <sub>B</sub>	base current (DC)		_	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	1.25	W
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>. For other mounting conditions, see *"Thermal considerations for the SOT223 in the General Part of associated Handbook"*.

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#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	96	K/W
R <sub>th j-s</sub>	thermal resistance from junction to solder point		17	K/W

#### Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>. For other mounting conditions, see "Thermal considerations for the SOT223 in the General Part of associated Handbook".

#### **CHARACTERISTICS**

 $T_i = 25$  °C unless otherwise specified.

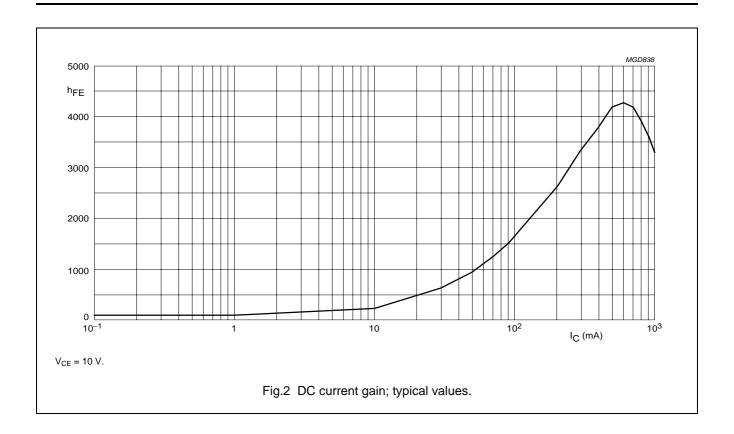
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CES</sub>	collector cut-off current					
	BSP50	$V_{BE} = 0; V_{CE} = 45 \text{ V}$	_	_	50	nA
	BSP51	$V_{BE} = 0; V_{CE} = 60 \text{ V}$	_	_	50	nA
	BSP52	V <sub>BE</sub> = 0; V <sub>CE</sub> = 80 V	_	_	50	nA
I <sub>EBO</sub>	emitter cut-off current	I <sub>C</sub> = 0; V <sub>EB</sub> = 4 V	_	_	50	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V; note 1; see Fig.2				
		I <sub>C</sub> = 150 mA	1000	_	_	
		I <sub>C</sub> = 500 mA	2000	_	_	
V <sub>CEsat</sub>	collector-emitter saturation	$I_C = 500 \text{ mA}; I_B = 0.5 \text{ mA}$	_	_	1.3	V
voltage		$I_C = 500 \text{ mA}; I_B = 0.5 \text{ mA};$ $T_j = 150 \text{ °C}$	_	_	1.3	V
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 500 mA; I <sub>B</sub> = 0.5 mA	_	_	1.9	V
f <sub>T</sub>	transition frequency	$I_C = 500 \text{ mA}; V_{CE} = 5 \text{ V}; f = 100 \text{ MHz}$	_	200	-	MHz
Switching times (between 10% and 90% levels); see Fig.3						
t <sub>on</sub>	turn-on time	I <sub>Con</sub> = 500 mA; I <sub>Bon</sub> = 0.5 mA;	_	500	_	ns
t <sub>off</sub>	turn-off time	$I_{Boff} = -0.5 \text{ mA}$	_	1300	-	ns

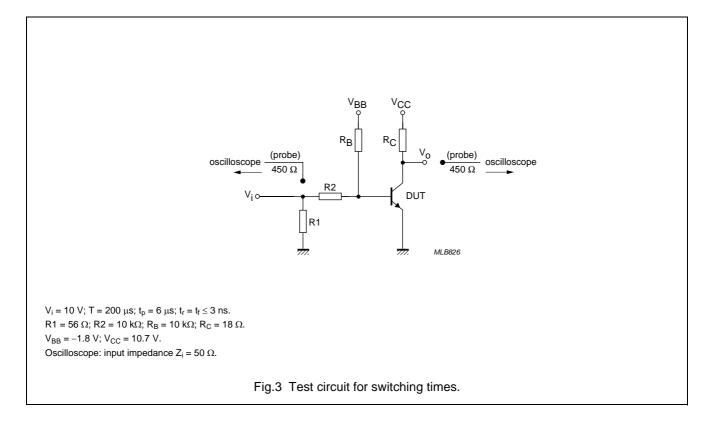
#### Note

1. Pulse test:  $t_p \leq 300~\mu s;~\delta \leq 0.02.$ 

## NPN Darlington transistors

BSP50; BSP51; BSP52





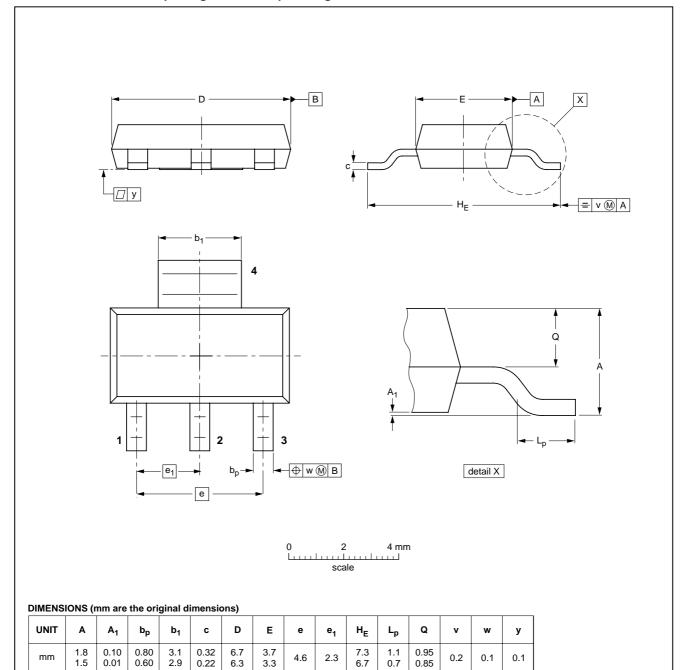
## NPN Darlington transistors

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#### **PACKAGE OUTLINE**

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

**SOT223** 



OUTLINE	REFERENCES			EUROPEAN	ICCUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT223			SC-73			<del>97-02-28</del> 99-09-13

### **NPN Darlington transistors**

BSP50; BSP51; BSP52

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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#### **Customer notification**

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#### **Contact information**

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